40V NPN SURFACE MOUNT TRANSISTOR

Features

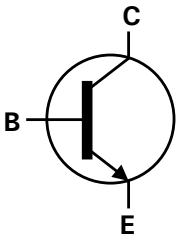
- Complementary PNP Type Available (MMBT3906LP)
- Ultra-Small Leadless Surface Mount Package
- **"Lead Free", RoHS Compliant (Note 1)**
- **Halogen and Antimony Free "Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

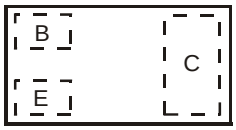
- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0008 grams (approximate)

X1-DFN1006-3

Bottom View



Device Symbol



Top View
Device Schematic

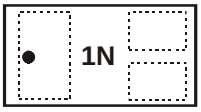
Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBT3904LP-7	1N	7	8mm	3,000
MMBT3904LP-7B	1N	7	8mm	10,000

Notes:
1. No purposefully added lead.
2. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com.
3. For packaging details, go to our website at http://www.diodes.com.

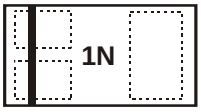
Marking Information

MMBT3904LP-7



Top View
Dot Denotes
Collector Side

MMBT3904LP-7B



Top View
Bar Denotes Base
and Emitter Side

1N = Product Type Marking Code

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous (Note 4)	I_C	200	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	P_D	250	mW
Thermal Resistance, Junction to Ambient (Note 4)	$R_{\theta JA}$	500	°C/W
Operating and Storage and Temperature Range	T_J, T_{STG}	-55 to +150	°C

Notes: 4. Device mounted on FR-4 PCB pad layout as shown on Diodes, Inc. suggested pad layout AP02001, which can be found on our website at http://www.diodes.com

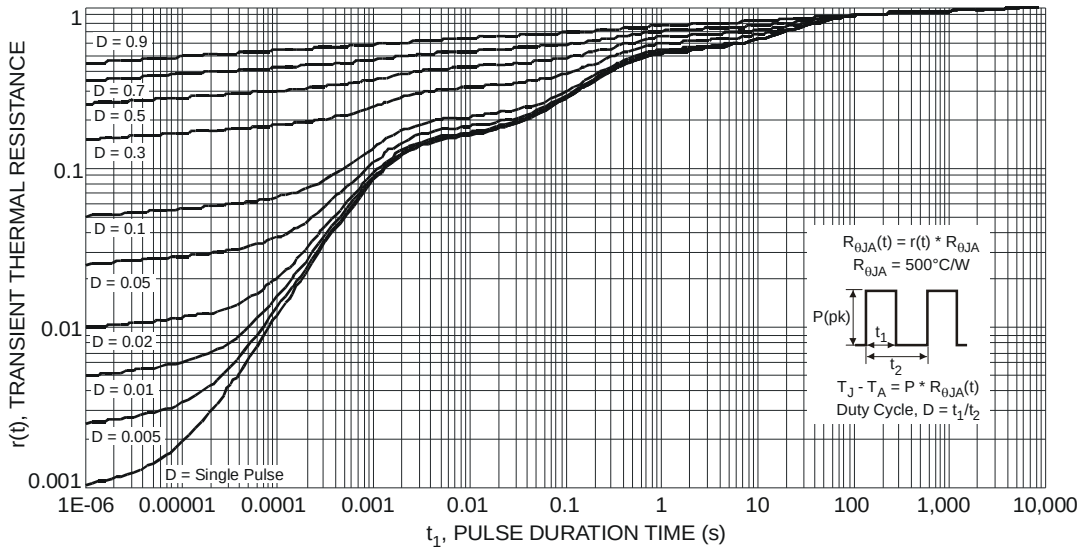


Fig. 1 Transient Thermal Response

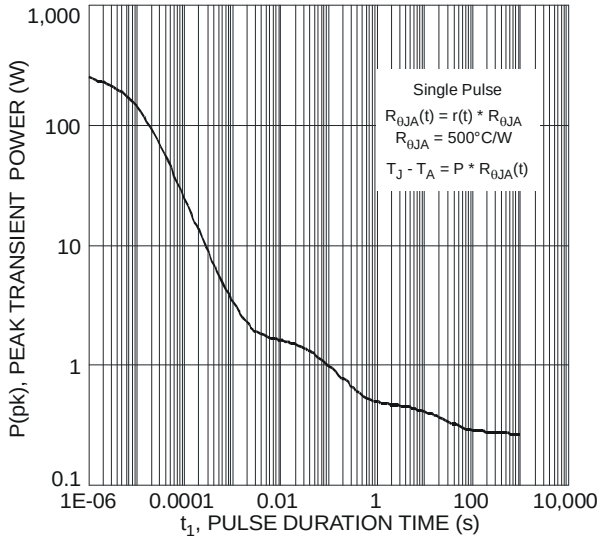


Fig. 2 Single Pulse Maximum Power Dissipation

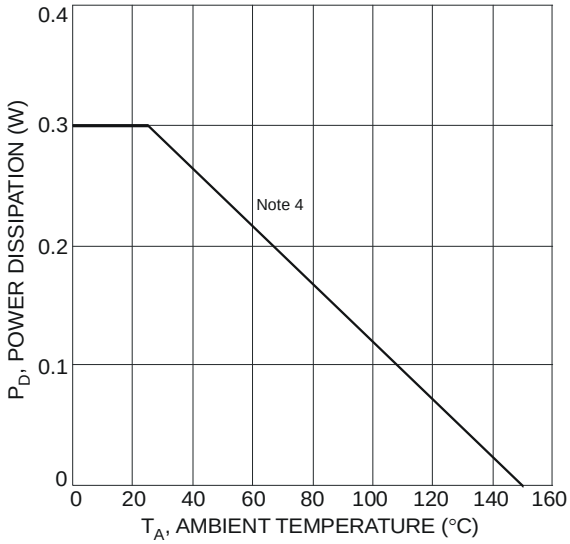


Fig. 3 Power Dissipation vs. Ambient Temperature

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV_{CBO}	60	—	V	I_C = 10μA, I_E = 0
Collector-Emitter Breakdown Voltage (Note 5)	BV_{CEO}	40	—	V	I_C = 1.0mA, I_B = 0
Emitter-Base Breakdown Voltage	BV_{EBO}	6.0	—	V	I_E = 10μA, I_C = 0
Collector Cutoff Current	I_{CEX}	—	50	nA	V_{CE} = 30V, $V_{EB(OFF)}$ = 3.0V
Base Cutoff Current	I_{BL}	—	50	nA	V_{CE} = 30V, $V_{EB(OFF)}$ = 3.0V
ON CHARACTERISTICS (Note 5)					
DC Current Gain	h_{FE}	40 70 100 60 30	— — 300 — —	—	I_C = 100μA, V_{CE} = 1.0V I_C = 1.0mA, V_{CE} = 1.0V I_C = 10mA, V_{CE} = 1.0V I_C = 50mA, V_{CE} = 1.0V I_C = 100mA, V_{CE} = 1.0V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	0.20 0.30	V	I_C = 10mA, I_B = 1.0mA I_C = 50mA, I_B = 5.0mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	0.65 —	0.85 0.95	V	I_C = 10mA, I_B = 1.0mA I_C = 50mA, I_B = 5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	—	4.0	pF	V_{CB} = 5.0V, f = 1.0MHz, I_E = 0
Input Capacitance	C_{ibo}	—	8.5	pF	V_{EB} = 0.5V, f = 1.0MHz, I_C = 0
Input Impedance	h_{ie}	1.0	10	kΩ	V_{CE} = 10V, I_C = 1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h_{re}	0.5	8.0	x 10^{-4}	
Small Signal Current Gain	h_{fe}	100	400	—	
Output Admittance	h_{oe}	1.0	40	μS	
Current Gain-Bandwidth Product	f_T	300	—	MHz	V_{CE} = 20V, I_C = 10mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	35	ns	V_{CC} = 3.0V, I_C = 10mA, $V_{BE(off)}$ = - 0.5V, I_{B1} = 1.0mA
Rise Time	t_r	—	35	ns	
Storage Time	t_s	—	200	ns	V_{CC} = 3.0V, I_C = 10mA, I_{B1} = I_{B2} = 1.0mA
Fall Time	t_f	—	50	ns	

Notes: 5. Short duration pulse test used to minimize self-heating effect.

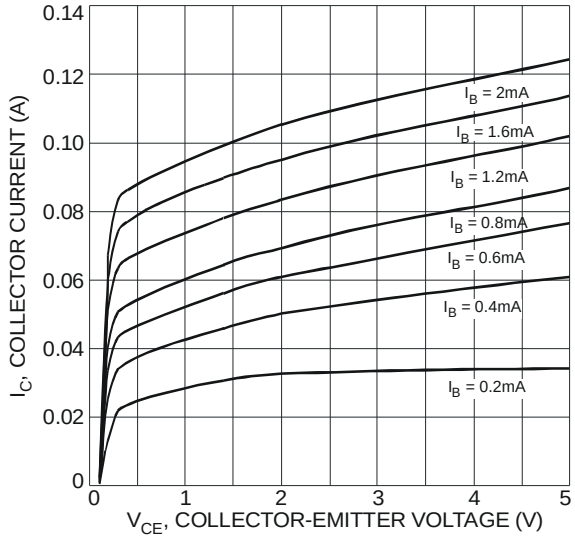


Fig. 4 Typical Collector Current vs. Collector-Emitter Voltage

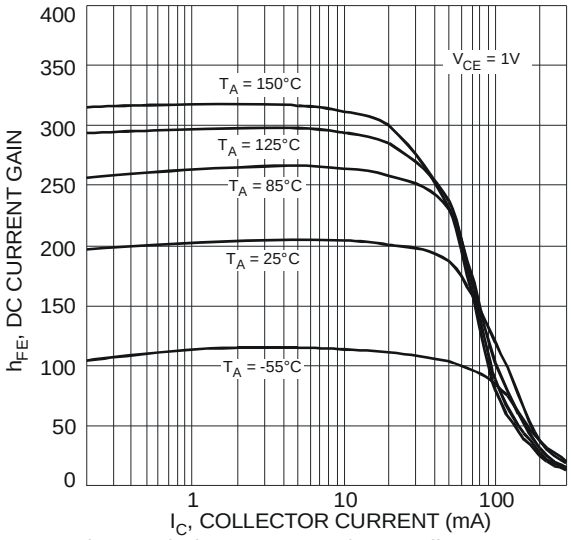


Fig. 5 Typical DC Current Gain vs. Collector Current

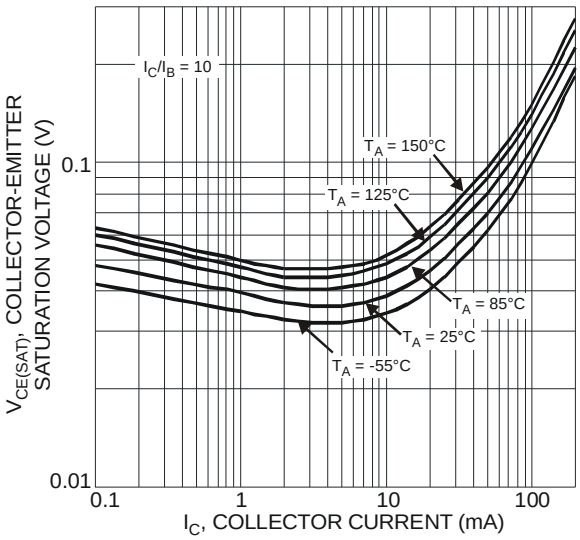


Fig. 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current

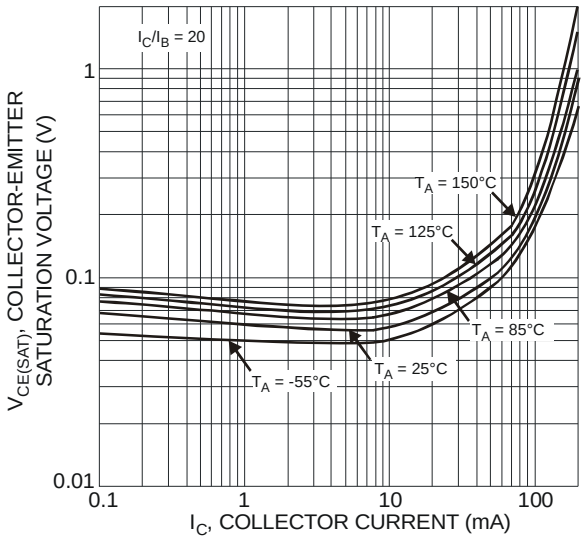


Fig. 7 Typical Collector-Emitter Saturation Voltage vs. Collector Current

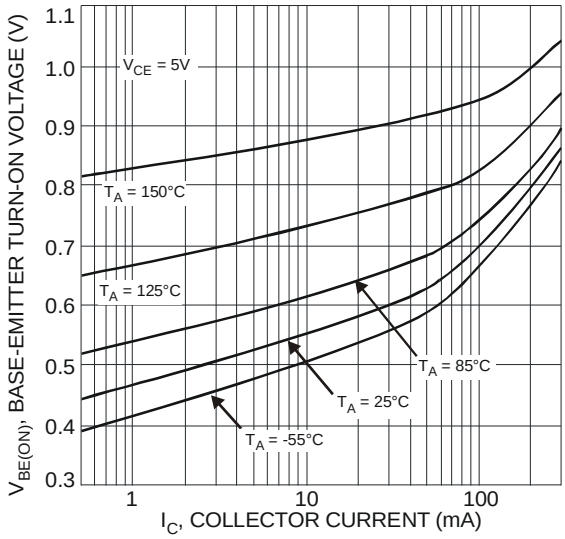


Fig. 8 Typical Base-Emitter Turn-On Voltage vs. Collector Current

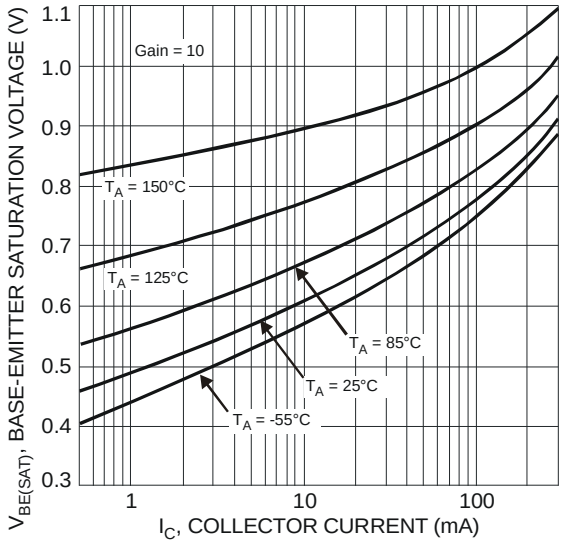
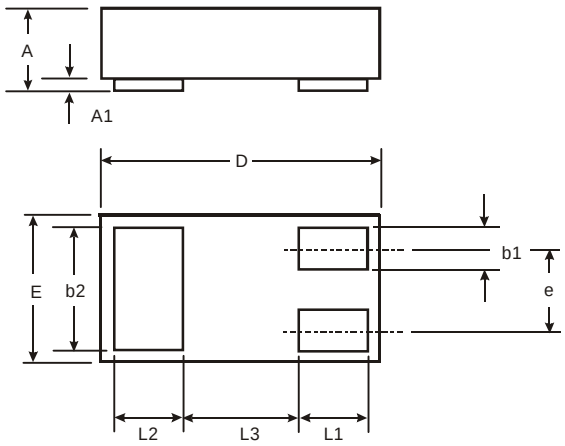


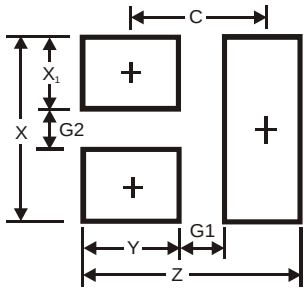
Fig. 9 Typical Base-Emitter Saturation Voltage vs. Collector Current

Package Outline Dimensions



X1-DFN1006-3			
Dim	**Min**	**Max**	**Typ**
A	0.47	0.53	0.50
A1	0	0.05	0.03
b1	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	—	—	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	—	—	0.40
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.1
G1	0.3
G2	0.2
X	0.7
X1	0.25
Y	0.4
C	0.7

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